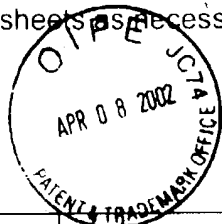


PTO/SB/08A			<b>Complete if Known</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			Application Number	10/039,196	
			Filing Date	January 2, 2002	
			Confirmation Number	7221	
			First Named Inventor	Robert J. Falster	
			Group Art Unit	1765	
			Examiner Name		
Sheet	1	of	2	Attorney Docket No.	MEMC 00-1400 (2806.1)



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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
	1	5,919,302		Falster et al.	07-06-1999
	2	5,994,761		Falster et al.	11-30-1999
	3	6,180,220		Falster et al.	01-30-2001
	4	6,191,010		Falster	02-20-2001
	5	6,254,672		Falster et al.	07-03-2001
	6	6,287,380		Falster et al.	09-11-2001
	7	6,336,968		Falster	01-08-2002
OTHER ART - NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>3</sup>
	8	R. FALSTER "The Phenomenology of Dielectric Breakdown in Thin Silicon Dioxide Films: Al Cathodes and p-type Si Anodes" J. Appl. Phys., Vol. 66, No. 7 (1989) pp. 3355-3370.			
	9	R. FALSTER et al. "On the Properties of the Intrinsic Point Defects in Silicon: A Perspective from Crystal Growth and Wafer Processing" Phys. Stat. Sol. (b), Vol. 222, No. 1 (2000) pp. 219-244.			

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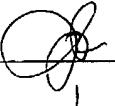
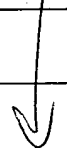

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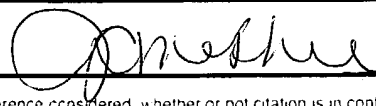
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OTHER ART - NON PATENT LITERATURE DOCUMENTS			
	10	T. SINNO et al. "Point Defect Dynamics and the Oxidation-Induced Stacking-Fault Ring in Czochralski-Grown Silicon Crystals" J. Electrochem. Soc., Vol. 145, No. 1 (1998) pp. 302-318.	
	11	A. VIRZI "Computer Modelling of Heat Transfer in Czochralski Silicon Crystal Growth" J. of Crystal Growth, Vol. 112, No. 4 (1991) pp. 699-722.	
	12	V. VORONKOV et al. "Grown-in Microdefects, Residual Vacancies and Oxygen Precipitation Bands in Czochralski Silicon" J. of Crystal Growth, Vol. 204 (1999) pp. 462-474.	
	13	V. VORONKOV et al. "Vacancy and Self-interstitial Concentration Incorporated into Growing Silicon Crystals" J. of Applied Physics, Vol. 86, No. 11 (1999) pp. 2975-2982.	
	14	V. VORONKOV et al. "Vacancy-type Microdefect Formation in Czochralski Silicon" J. of Crystal Growth, Vol. 194 (1998) pp. 76-88.	

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